In the Specification:

Please amend paragraph 1 as follows:

This application is related to U.S. Patent Application No. 10/713,878 ~~(Attorney Docket No. 10829.8742US00; Micron Disclosure Nos. 03-0599 and 03-0613)~~ entitled MICROELECTRONIC DEVICES, METHODS FOR FORMING VIAS IN MICROELECTRONIC DEVICES, AND METHODS FOR PACKAGING MICROELECTRONIC DEVICES, filed November 13, 2003, ~~concurrently herewith~~ and incorporated herein in its entirety by reference.

Please amend paragraph 27 as follows:

Figure 3 is a schematic cross-sectional view of the microelectronic device 210b taken substantially along line 3-3 in Figure 2 in accordance with an embodiment of the invention. The microelectronic device 210b is inverted in Figure 3 for purposes of illustration, and it has undergone additional processing beyond that illustrated in Figure 2. For example, in one aspect of this embodiment, the microelectronic device 210b includes a via or passage 342 extending through the die 212 and the bond-pad 216. The passage 342 and the opening 218 define a first opening 346 in the front side 201 of the microfeature workpiece 200, and a second opening 348 in the back side 202. In one embodiment, the passage 342 can be formed using a laser-cutting method at least generally similar to one or more of the methods described in co-pending U.S. Patent Application No. 10/713,878~~(Attorney Docket No. 10829.8742US00)~~, entitled MICROELECTRONIC DEVICES, METHODS FOR FORMING VIAS IN MICROELECTRONIC DEVICES, AND METHODS FOR PACKAGING MICROELECTRONIC DEVICES. In other embodiments, the passage 342 can be formed using other methods, such as a suitable etching or drilling method. Although, in one embodiment, the passage 342 may be slightly tapered as depicted in Figure 3, in other embodiments, the passage 342 can be straight or at least approximately straight.

Please amend paragraph 38 as follows:

Referring next to Figure 7B, after the metallic layer 780 has been deposited on the microelectronic device 610, the conductive element 650 is positioned against the metallic layer 780. As discussed above, the conductive element 650 can be a plate electrode or a conductive polymer configured to apply an electrical bias to the metallic layer 780, which in turn biases the plug 660. The conductive element 650, however, can be a finger type contact as shown in U.S. ~~Application~~ Patent No. 6,080,291, which is herein incorporated by reference. Electrically biasing the plug 660 facilitates electroplating a second portion of conductive material 745 in the passage 642 adjacent to the plug 660. Together, the plug 660 and the second portion of conductive material 745 form a conductive interconnect 746 extending through the microelectronic device 610.